

N-channel 40 V 1.3 mΩ standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product data

Product data sheet

Product profile 1.

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1.1 General description

Standard level N-channel MOSFET in D2PAK (SOT404) package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	40	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u> ;see <u>Figure 13</u>	-	1.68	2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	1.16	1.3	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 75 A; V_{DS} = 20 V;	-	32	-	nC
Q _{G(tot)}	total gate charge	see Figure 14;see Figure 15	-	136	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	1.4	J

[1] Continuous current is limited by package



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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	drain	ii	
				mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	number Package			
	Name	Description	Version	
PSMN1R1-40BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404	

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

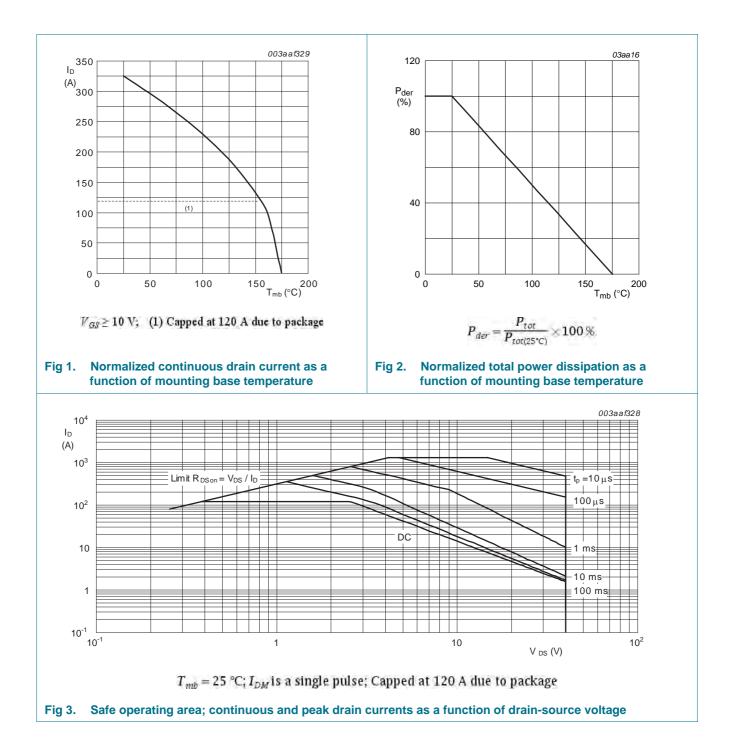
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C	<u>[1]</u>	-	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	1320	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-di	rain diode					
ls	source current	T _{mb} = 25 °C	<u>[1]</u>	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1320	А
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ I}_{D} = 120 \text{ A}; \text{ V}_{sup} \le 40 \text{ V};$ unclamped; $\text{R}_{GS} = 50 \Omega; \text{ t}_{p} = 0.1 \text{ ms}$		-	1.4	J

[1] Continuous current is limited by package.

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PSMN1R1-40BS

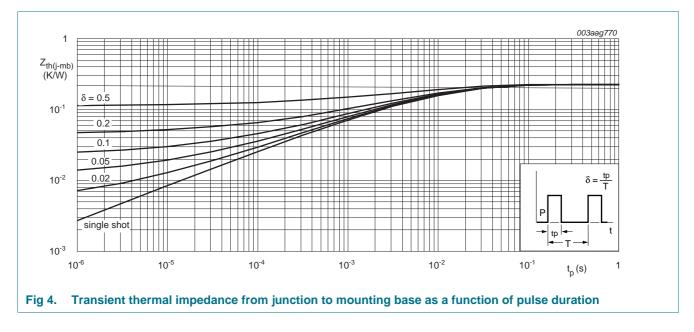
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N-channel 40 V 1.3 mΩ standard level MOSFET in D2PAK

5. Thermal characteristics

Table 5.	Thermal characteristics						
Symbol	Parameter	Parameter Conditions		Тур	Max	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W	



N-channel 40 V 1.3 mΩ standard level MOSFET in D2PAK

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11;see Figure 10	2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u> ;see <u>Figure 13</u>	-	1.68	2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12;see Figure 13	-	2.3	2.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	1.16	1.3	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	133	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	136	-	nC
Q _{GS}	gate-source charge	see Figure 14;see Figure 15	-	52	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	22	-	nC
Q _{GD}	gate-drain charge		-	32	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 75 \text{ A}; V_{DS} = 20 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	6.1	-	V
C _{iss}	input capacitance	V_{DS} = 20 V; V_{GS} = 0 V; f = 1 MHz;	-	9710	-	pF
C _{oss}	output capacitance	T _j = 25 °C;see <u>Figure 16</u>	-	2042	-	pF
C _{rss}	reverse transfer capacitance		-	994	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	66	-	ns
t _{d(off)}	turn-off delay time		-	111	-	ns
t _f	fall time		-	53	-	ns

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Symbol

Source-drain diode

PSMN1R1-40BS

Тур

Max

Unit

N-channel 40 V 1.3 m Ω standard level MOSFET in D2PAK

Min

D	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0$ see <u>Figure 17</u>	V; T _j = 25 °C; -	0.8	1.2	V
	reverse recovery time		$-100 \text{ A/}\mu\text{s}; \text{V}_{\text{GS}} = 0 \text{ V};$	64	-	ns
	recovered charge	V _{DS} = 20 V	-	117	-	nC
200 9 _{fs} (S) 150		003aaf316	75 I _D (A) 60		003aaf317	
100			45			
50			15 $T_{j} = 175$	5.0С Т	; = 25 °C	
o م	15 30	45 I _D (A) 60	0 0 2	4 V ₀	GS ^(V) 6	
	$T_j = 25 ^{\circ}C; V_{DS} = 25$	V	$V_{DS} > I_D$	$M \times R_{DSom}$		
	$T_j = 25 ^{\circ}C; V_{DS} = 25$ rward transconductance a in current; typical values	as a function of	V _{DS} >I _D Fig 6. Transfer characteris function of gate-sou	stics: drain		
	rward transconductance a		Fig 6. Transfer characteris	stics: drain o urce voltage		
dra 18000 C (pF)	rward transconductance a in current; typical values	003aaf320	Fig 6. Transfer characteris function of gate-sou	stics: drain o urce voltage	; typical	
dra	rward transconductance a in current; typical values	003aaf320	Fig 6. Transfer characteris function of gate-sou	stics: drain o urce voltage	; typical	
dra 18000 C (pF) 14000 10000	rward transconductance a in current; typical values	003aaf320	Fig 6. Transfer characteris function of gate-sou	stics: drain of urce voltage	; typical	values
dra 18000 C (pF) 14000 10000 6000 2000	rward transconductance a in current; typical values	as a function of	Fig 6. Transfer characteris function of gate-sou	stics: drain of urce voltage	; typical	value

Table 6. Characteristics ...continued

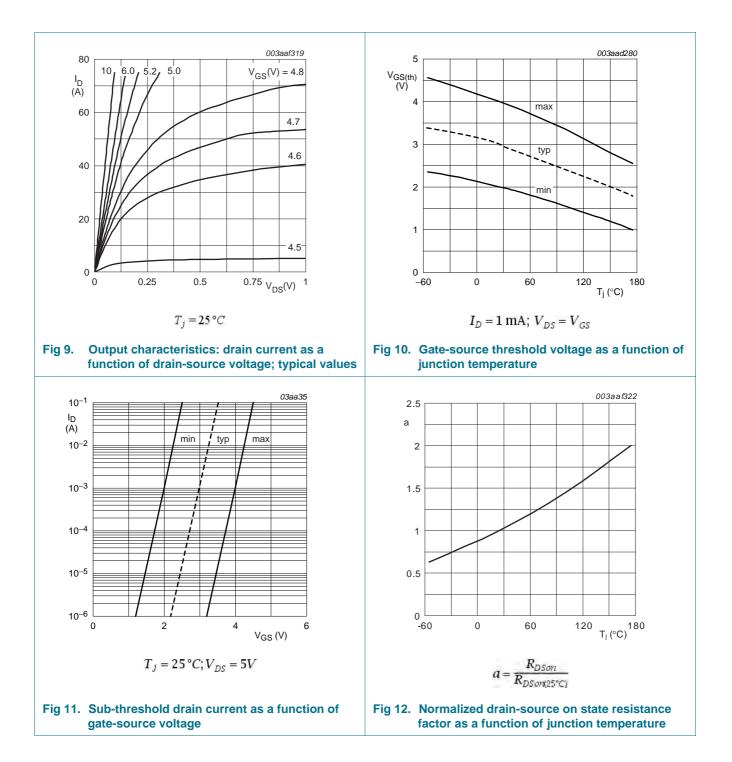
Parameter

Conditions

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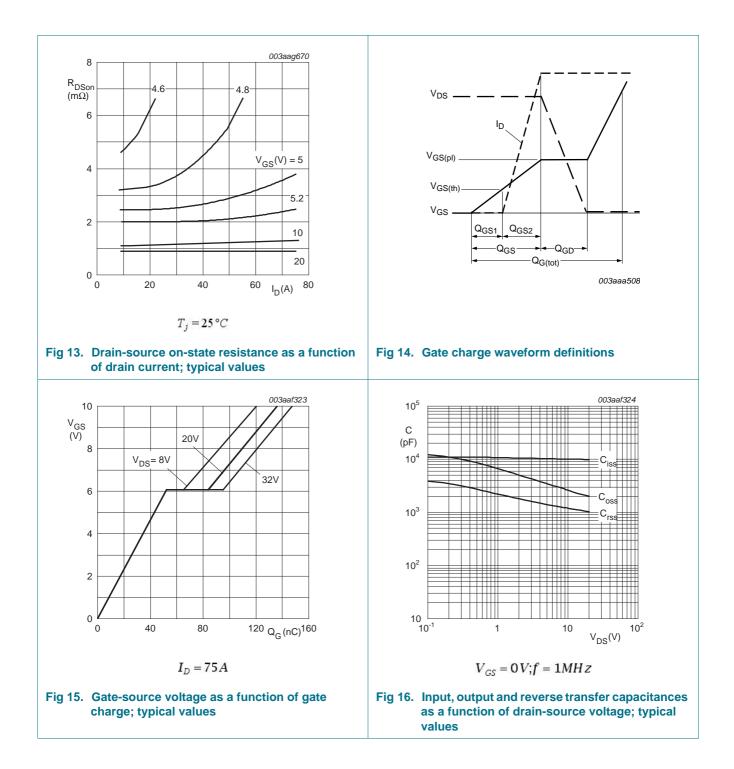
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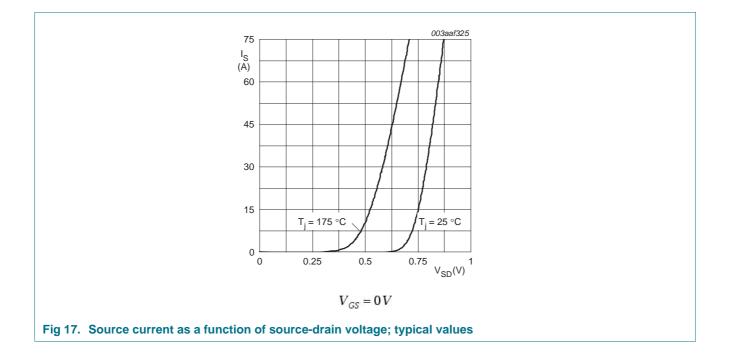
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7. Package outline

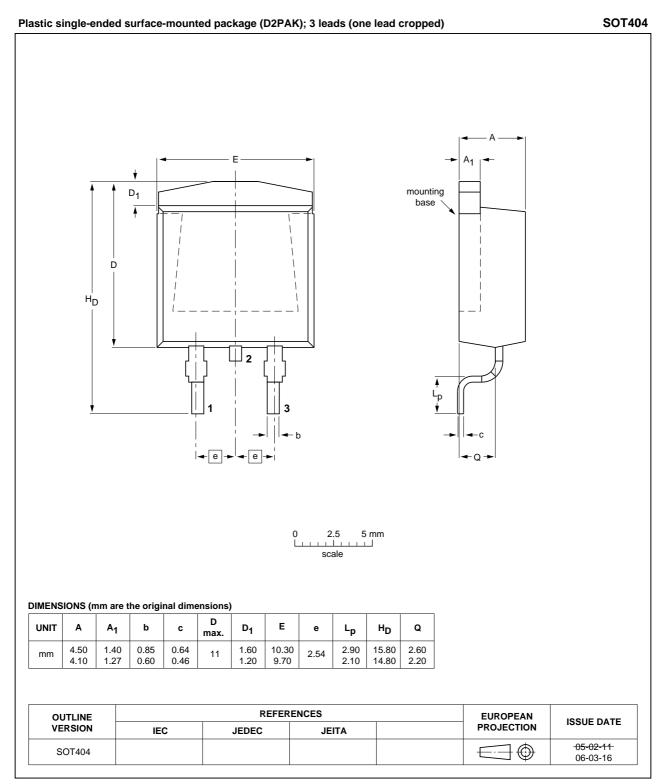


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R1-40BS v.2	20120229	Product data sheet	-	PSMN1R1-40BS v.1
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN1R1-40BS v.1	20110929	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

PSMN1R1-40BS

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11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status12
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13

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